Infrared Emitter (850 nm) Version 1.3

SFH 4356



Features:

- Wavelength 850nm
- Short switching times
- · Good spectral match to silicon photodetectors
- package similar to SFH 309

Applications

- · IR remote control
- Sensor technology
- · Discrete optocouplers
- · Discrete interrupters

Notes

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Ordering Information

Туре:	Radiant Intensity	Ordering Code
	I _e [mW/sr]	
	I _F = 100 mA, t _p = 20 ms	
SFH 4356	90 (≥ 40)	Q65111A6136
SFH 4356-UV	40 125	Q65111A8863

Note: measured at a solid angle of $\Omega = 0.01 \text{ sr}$



$\underline{\text{Maximum Ratings } (T_A = 25 \, ^{\circ}\text{C})}$

Parameter	Symbol	Values	Unit
Operation and storage temperature range	T _{op} ; T _{stg}	-40 100	°C
Reverse voltage	V _R	5	V
Forward current	I _F	100	mA
Surge current $(t_p \le 200 \ \mu s, D = 0)$	I _{FSM}	1	А
Power consumption	P _{tot}	200	mW
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V _{ESD}	2	kV
Thermal resistance junction - ambient 1) page 9	R _{thJA}	350	K/W
Thermal resistance junction - soldering point	R _{thJS}	150	K/W

Characteristics $(T_A = 25 \, ^{\circ}C)$

Parameter		Symbol	Values	Unit
Peak wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	λ_{peak}	860	nm
Centroid wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	$\lambda_{ ext{centroid}}$	850	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	Δλ	30	nm
Half angle	(typ)	φ	± 20	0
Dimensions of active chip area	(typ)	LxW	0.3 x 0.3	mm x mm
Rise and fall time of I_e (10% and 90% of $I_{e max}$) ($I_F = 100 \text{ mA}, R_L = 50 \Omega$)	(typ)	t _r , t _f	12	ns
Forward voltage $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ (max))	V _F	1.7 (≤ 2)	V
Forward voltage $(I_F = 1A, t_p = 100 \mu s)$	(typ (max))	V _F	3.6 (≤ 4.6)	V
Reverse current (V _R = 5 V)		I _R	not designed for reverse operation	μΑ
Total radiant flux (I _F =100 mA, t _p =20 ms)	(typ)	Фе	80	mW



Parameter		Symbol	Values	Unit
Temperature coefficient of I_e or Φ_e ($I_F = 100 \text{ mA}$, $I_p = 20 \text{ ms}$)	(typ)	TC _I	-0.3	% / K
Temperature coefficient of V_F ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	TC _V	-0.6	mV / K
Temperature coefficient of wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	TC _λ	0.3	nm / K

Grouping ($T_A = 25 \, ^{\circ}C$)

Group	Min Radiant Intensity	Max Radiant Intensity	Typ Radiant Intensity
	I _F = 100 mA, t _p = 20 ms	I _F = 100 mA, t _p = 20 ms	$I_F = 1 A, t_p = 100 \mu s$
	I _{e, min} [mW / sr]	I _{e, max} [mW / sr]	I _{e, typ} [mW / sr]
SFH 4356-U	40	80	255
SFH 4356-V	63	125	395
SFH 4356-AW	100	200	630
SFH 4356-BW	160	320	1000

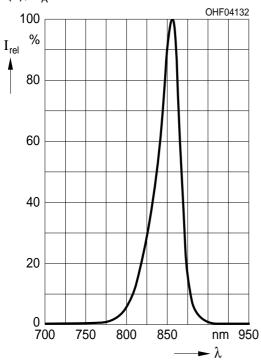
Note: Measured at a solid angle of $\Omega = 0.01$ sr

Only one group in one packing unit (variation lower 2:1).



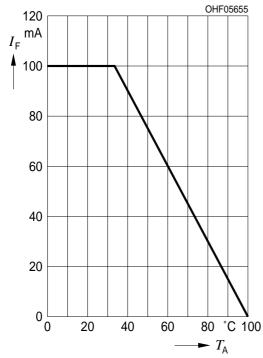
Relative Spectral Emission 2) page 9

 $I_{rel} = f(\lambda), T_A = 25^{\circ}C$



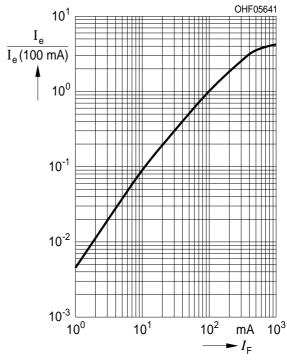
Max. Permissible Forward Current

 $I_{F, max} = f(T_A), R_{thJA} = 350 \text{ K} / \text{W}$



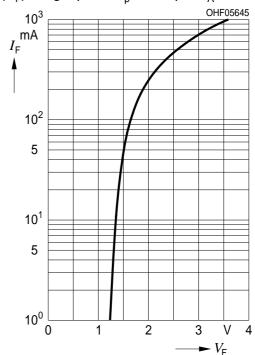
Radiant Intensity 2) page 9

 I_e / I_e (100 mA) = f(I_F), single pulse, t_p = 100 μ s, T_A = 25°C



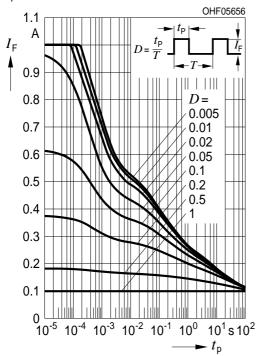
Forward Current 2) page 9

 $I_F = f(V_F)$, single pulse, $t_D = 100 \mu s$, $T_A = 25^{\circ} C$



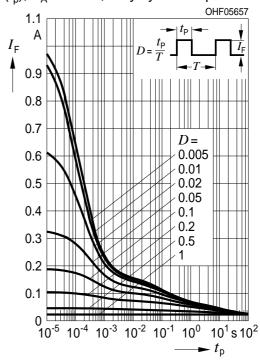
Permissible Pulse Handling Capability

 $I_F = f(t_p)$, $T_A = 25$ °C, duty cycle D = parameter



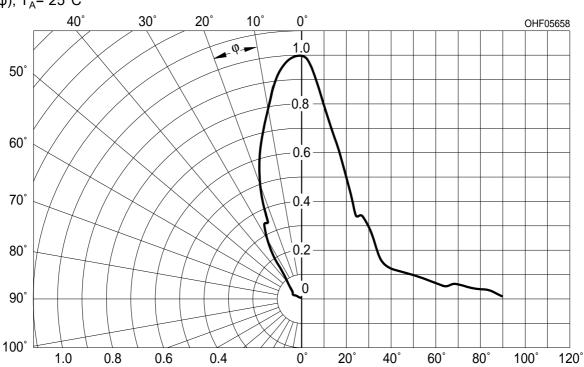
Permissible Pulse Handling Capability

 $I_F = f(t_p)$, $T_A = 85$ °C, duty cycle D = parameter

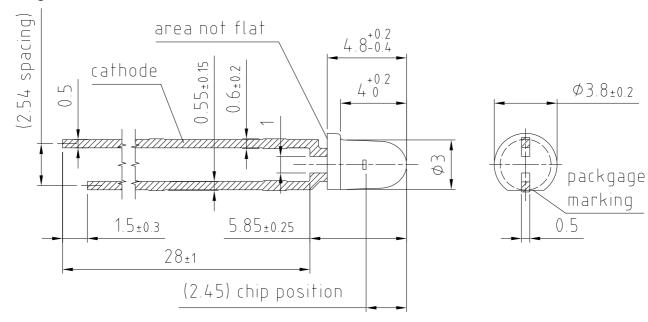


Radiation Characteristics 2) page 9

 $I_{rel} = f(\phi), T_A = 25^{\circ}C$



Package Outline



general tolerance ± 0.1 lead finish Sn

Dimensions in mm.

Package

3mm Radial (T 1), Epoxy, black

Approximate Weight:

0.2 g

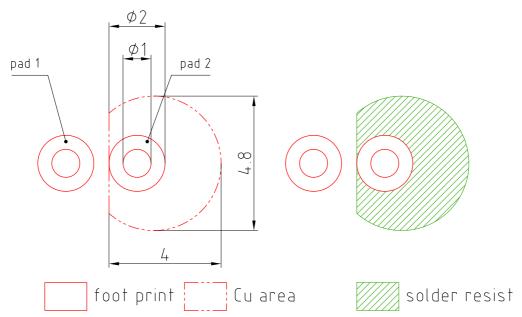
Note

Packing information is available on the internet (online product catalog).



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Recommended Solder Pad



E062.3010.188-01

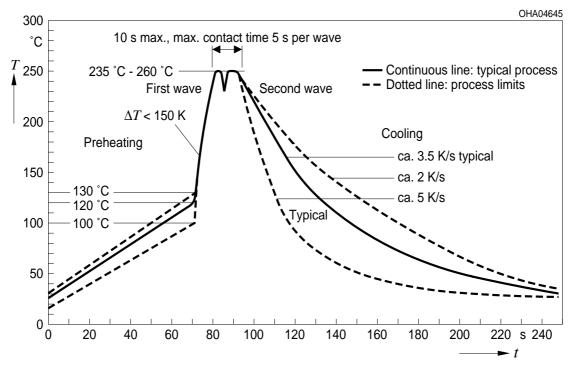
Dimensions in mm.

Note:

pad 1: cathode

TTW Soldering

IEC-61760-1 TTW



Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version in the Internet.

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- *) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.
- **) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.



Glossary

1) Thermal resistance: junction -ambient, mounted on PC-board (FR4), padsize 16 mm² each

Typical Values: Due to the special conditions of the manufacturing processes of LED, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.

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